NSN 5962-01-372-9624

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Maximum Power Dissipation Rating:
1.2 watts
Operating Tempurature Range:
-55.0/+125.0 degrees celsius
Storage Tempurature Range:
-65.0/+150.0 degrees celsius
Features Provided:
Bipolar and programmed
Inclosure Material:
Ceramic
Inclosure Configuration:
Leadless flat pack
Output Logic Form:
Bipolar metal-oxide semiconductor
Input Circuit Pattern:
20 input
Case Outline Source And Designator:
C-4 mil-m-38510
Current Rating Per Characteristic:
100.00 milliamperes reverse current, dc
Terminal Surface Treatment:
Solder
Product Name:
Microcircuit, programmed pal
Voltage Rating And Type Per Characteristic:
-0.5 volts total supply and 7.0 volts total supply
Memory Device Type:
Pal
Hybrid Toobhology Typo

Hybrid Technology Type:

Monolithic

Test Data Document:

81349-mil-m-38510 specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specification format; excludes commercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain environmental and performance requirements and test conditions that are shown as "typical", "average", "", etc.). And 96906-mil-std-883 standard (includes industry or association standards, individual manufactureer standards, etc.).

Terminal Type And Quantity:

28 printed circuit

Specification Data:

67268-5962-87671013a government standard

Purchase Description Identification:

04939-79931053-001

Departure From Cited Designator:

Altered by programming & marking

Shelf Life:

N/a

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Unit Of Measure:

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Demilitarization:

Yes - demil/mli

Fiig:

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